

V_{COM} with Dual Gamma Buffer



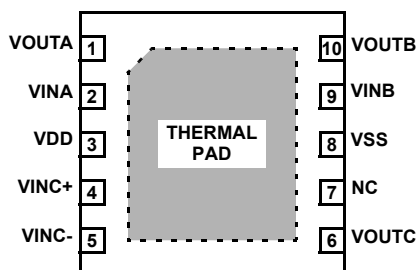
The EL5228 integrates a high power V_{COM} amplifier with dual gamma reference voltage buffers. With 180mA

peak and 65mA typical output current, the V_{COM} amplifier is suitable for all sizes of LCD displays. The dual gamma buffers can output 30mA typical, 120mA peak and feature a bandwidth of 12MHz and a slew rate of 15V/μs. The V_{COM} amplifier has a 44MHz bandwidth and 80V/μs slew rate.

The EL5228 operates from just 3.5mA typical supply current and is packaged in the high-power DFN-10 package. It is specified for operation over the -40°C to +85°C temperature range.

Pinout

EL5228
(10-PIN DFN)
TOP VIEW
TOP VIEW



Features

- High power V_{COM} amplifier
 - 180mA peak (65mA typ.) output current
 - 55MHz bandwidth
 - 75V/μs slew rate
- Dual gamma buffers
 - 120mA peak (30mA typ.) output current
 - 12MHz bandwidth
 - 10V/μs slew rate
- Just 3.5mA supply current
- Small DFN-10 package

Applications

- TFT-LCD displays
- Flat panel monitors
- Notebook displays
- LCD-TVs

Ordering Information

PART NUMBER	PACKAGE	TAPE & REEL	PKG. DWG. #
EL5228IL	10-Pin DFN	-	MDP0047
EL5228IL-T13	10-Pin DFN	13"	MDP0047
EL5228IL-T7	10-Pin DFN	7"	MDP0047

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

V_{CC} Supply Voltage between VS and GND TBD
 Supply Voltage between VSD and GND TBD
 Maximum Continuous Output Current TBD
 Ambient Operating Temperature TBD

Maximum Die Temperature TBD
 Storage Temperature TBD
 Power Dissipation See Curves

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$

Electrical Specifications $V_{S+} = +15\text{V}$, $V_{S-} = 0\text{V}$, $R_L = 1\text{k}\Omega$ to 7.5V , $T_A = 25^\circ\text{C}$ unless otherwise specified.

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
GAMMA BUFFER INPUT CHARACTERISTICS						
V_{OS}	Input Offset Voltage	$V_{CM} = 7.5\text{V}$		2	14	mV
TCV_{OS}	Average Offset Voltage Drift	(Note 1)		5		$\mu\text{V}/^\circ\text{C}$
I_B	Input Bias Current	$V_{CM} = 7.5\text{V}$		2	50	nA
R_{IN}	Input Impedance			1		$\text{G}\Omega$
C_{IN}	Input Capacitance			2		pF
A_V	Voltage Gain	$0.5 \leq V_{OUT} \leq 14.5\text{V}$, $R_L = 10\text{k}\Omega$	0.995		1.005	V/V
GAMMA BUFFER OUTPUT CHARACTERISTICS						
V_{OL}	Output Swing Low	$I_L = -5\text{mA}$		80	150	mV
V_{OH}	Output Swing High	$I_L = 5\text{mA}$	14.85	14.92		V
I_{SC}	Short Circuit Current	Short to GND (Note 2)	± 80	± 120		mA
GAMMA BUFFER DYNAMIC PERFORMANCE						
SR	Slew Rate (Note 3)	$1\text{V} \leq V_{OUT} \leq 14\text{V}$, 20% to 80%, $R_L = 10\text{k}\Omega$	7	10		V/ μs
t_S	Settling to $\pm 0.1\%$	$V_O = 2\text{V}$ Step		500		ns
BW	-3dB Bandwidth	$R_L = 10\text{k}\Omega$, $C_L = 10\text{pF}$		12		MHz
CS	Channel Separation	$f = 5\text{MHz}$		75		dB
V_{COM} AMPLIFIER INPUT CHARACTERISTICS						
V_{OS}	Input Offset Voltage	$V_{CM} = 7.5\text{V}$		3	15	mV
TCV_{OS}	Average Offset Voltage Drift (Note 4)			7		$\mu\text{V}/^\circ\text{C}$
I_B	Input Bias Current	$V_{CM} = 7.5\text{V}$		2	60	nA
R_{IN}	Input Impedance			1		$\text{G}\Omega$
C_{IN}	Input Capacitance			2		pF
CMIR	Common-Mode Input Range		-0.5		+15.5	V
CMRR	Common-Mode Rejection Ratio	for V_{IN} from -0.5V to 15.5V	53	72		dB
A_{VOL}	Open-Loop Gain	$0.5\text{V} \leq V_{OUT} \leq 14.5\text{V}$	62	70		dB
V_{COM} AMPLIFIER OUTPUT CHARACTERISTICS						
V_{OL}	Output Swing Low	$I_L = -5\text{mA}$		80	150	mV
V_{OH}	Output Swing High	$I_L = 5\text{mA}$	14.85	14.92		V
I_{SC}	Short-circuit Current			± 180		mA
I_{OUT}	Output Current			± 65		mA

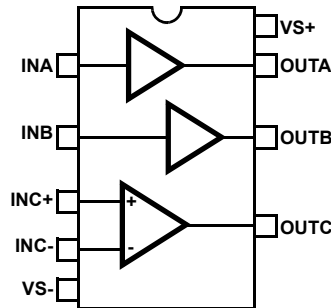
Electrical Specifications $V_{S+} = +15V$, $V_{S-} = 0V$, $R_L = 1k\Omega$ to $7.5V$, $T_A = 25^\circ C$ unless otherwise specified.

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
V_{COM} AMPLIFIER DYNAMIC PERFORMANCE						
SR	Slew Rate (Note 5)	$1V \leq V_{OUT} \leq 14V$, 20% to 80%		75		V/ μs
t_S	Settling to +0.1% ($A_V = +1$)	($A_V = +1$), $V_O = 2V$ step		80		ns
BW	-3dB Bandwidth			60		MHz
GBWP	Gain-Bandwidth Product			32		MHz
PM	Phase Margin			50		°
d_G	Differential Gain (Note 6)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.16		%
d_P	Differential Phase (Note 6)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.22		°
POWER SUPPLY PERFORMANCE						
PSRR	Power Supply Rejection Ratio	V_S is moved from 4.5V to 15.5V	60	80		dB
I_S	Supply Current	No load		3.5	5	mA

NOTES:

1. Measured over the operating temperature range
2. Parameter is guaranteed (but not test) by design and characterization data
3. Slew rate is measured on rising and falling edges
4. Measured over operating temperature range
5. Slew rate is measured on rising and falling edges
6. NTSC signal generator used

Typical Application Diagram



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